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Term	Documents
ATOMIC.USPT,PGPB.	61110
ATOMICS.USPT,PGPB.	285
LAYER.USPT,PGPB.	669947
LAYERS.USPT,PGPB.	386301
DEPOSITION.USPT,PGPB.	165288
DEPOSITIONS.USPT,PGPB.	6980
EPITAXY.USPT,PGPB.	11041
EPITAXIES.USPT,PGPB.	37
EPITAXYS	0
ALE.USPT,PGPB.	2202
(((ATOMIC LAYER NEAR2 (DEPOSITION OR EPITAXY)) OR ALE OR ALD) AND (HFZRO)).USPT,PGPB.	0

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Database:

- US Patents Full-Text Database
- US Pre-Grant Publication Full-Text Database
- JPO Abstracts Database
- EPO Abstracts Database
- Derwent World Patents Index
- IBM Technical Disclosure Bulletins

Refine Search:

((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (HfZrO)

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<u>DB Name</u>	<u>Query</u>	<u>Hit Count</u>	<u>Set Name</u>
USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (HfZrO)	0	<u>L39</u>

USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (ZrHfO)	0	L38
USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (Zr near2 Hf near2 O)	0	L37
USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (zirconium near2 hafnium near2 oxide)	5	L36
JPAB,EPAB,DWPI,TDBD	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (zirconium near2 hafnium near2 oxide)	0	L35
USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and semiconductor and (zirconium near2 hafnium near2 oxide)	4	L34
USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and ((radiation or photo\$8 or light) same (heat near2 treat\$4))	20	L33
JPAB,EPAB,DWPI,TDBD	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (radiation or photo\$8 or light) and ((anneal\$3) or (heat near2 treat\$4))	0	L32
USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and ((radiation or photo\$8 or light) same (anneal\$3))	26	L31
JPAB,EPAB,DWPI,TDBD	L7 and radiation	3	L30
USPT,PGPB	L28 and purg\$3	11	L29
USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (radiation) and puls\$3	111	L28
USPT,PGPB	L26 and (purg\$3)	17	L27
USPT,PGPB	L18 and semiconductor	235	L26
USPT,PGPB	5138520.pn.	1	L25
USPT,PGPB	4058430.pn.	1	L24
USPT,PGPB	4058030.pn.	1	L23
JPAB,EPAB,DWPI,TDBD	(puls\$3) and (purg\$3 same inert) and (photo\$8 or light) and (gas or vapor)	1	L22
USPT,PGPB	((precursor or feed) near3 puls\$3) and (purg\$3 same inert) and (photo\$8 or light)	13	L21
USPT,PGPB	L18 and (purg\$3 same inert)	6	L20
USPT,PGPB	L8 and (purg\$3 same inert)	0	L19
USPT,PGPB	((atomic layer near2 (deposition or epitaxy)) or ALE or ALD) and (photo\$8 or light) and puls\$3	560	L18
USPT	4678536	23	L17
USPT	4678536.pn.	1	L16
JPAB,DWPI	2208925	5	L15
JPAB,DWPI	63055929	2	L14

JPAB,DWPI	61124123	2	<u>L13</u>
JPAB,DWPI	60016416	2	<u>L12</u>
JPAB,DWPI	6016416	2	<u>L11</u>
JPAB,DWPI	5904829	1	<u>L10</u>
USPT,PGPB	5443033.pn.	1	<u>L9</u>
USPT,PGPB	5705224	1	<u>L8</u>
JPAB,EPAB,DWPI,TDBD	((photo\$8) or light) and (ALE or ALD or (atomic near3 (epitaxy or deposition)))	89	<u>L7</u>
JPAB,EPAB,DWPI,TDBD	((photo\$8) or (puls\$3) or light) and (ALE or ALD or (atomic near3 (epitaxy or deposition)))	140	<u>L6</u>
JPAB,EPAB,DWPI,TDBD	((photo\$8) or (puls\$3) or light) and (ALE or ALD or (atomic near4 (epitaxy or deposition)))	149	<u>L5</u>
JPAB,EPAB,DWPI,TDBD	(photo\$8) and (puls\$3) and light and (ALE or ALD or (atomic near4 (epitaxy or deposition)))	2	<u>L4</u>
USPT,PGPB	L1 and (pulse or pulsed or pulsing)	16	<u>L3</u>
USPT,PGPB	L1 and (ALE or ALD or (atomic near4 (epitaxy or deposition)))	0	<u>L2</u>
USPT,PGPB	((427/582)!.ICLS.)	47	<u>L1</u>